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(71) Applicant (for all designated States except US): **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, California 94538 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **Ji, Bing** [US/US]; 2887 Garden Creek Circle, Pleasanton, California 94588 (US). **TAKESHITA, Kenji** [JP/US]; 1471 Yukon Drive, Sunnyvale, California 94087 (US). **BAILEY, Andrew D., III** [US/US]; 3363 Sagewood Court, Pleasanton, California 94588 (US). **HUDSON, Eric A.** [US/US]; 1820 Catalina Avenue, Berkeley, California 94707 (US). **MORAVEJ, Maryam** [US/US]; 707 Astor Court, Mountain View, California 94043 (US). **SIRARD, Stephen M.** [US/US]; 7136 Chimney Cors, Austin, Texas 78731 (US). **KO, Jungmin** [KR/US]; 777 W. Middlefield Road, Apt. 71, Mountain View, California 94043 (US). **LE, Daniel** [US/US]; 1224 Carmel Way, Santa Clara, California 95050 (US). **HEFTY, Robert C.** [US/US]; 29721 Ivy Glenn, Laguna Niguel, California 92677 (US). **CHENG, Yu** [CN/US]; 40758 Chiltren Drive, Fremont, California 94539 (US). **DELGADINO, Gerardo A.** [US/US]; 1323

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(54) Title: METHOD FOR LOW-K DIELECTRIC ETCH WITH REDUCED DAMAGE

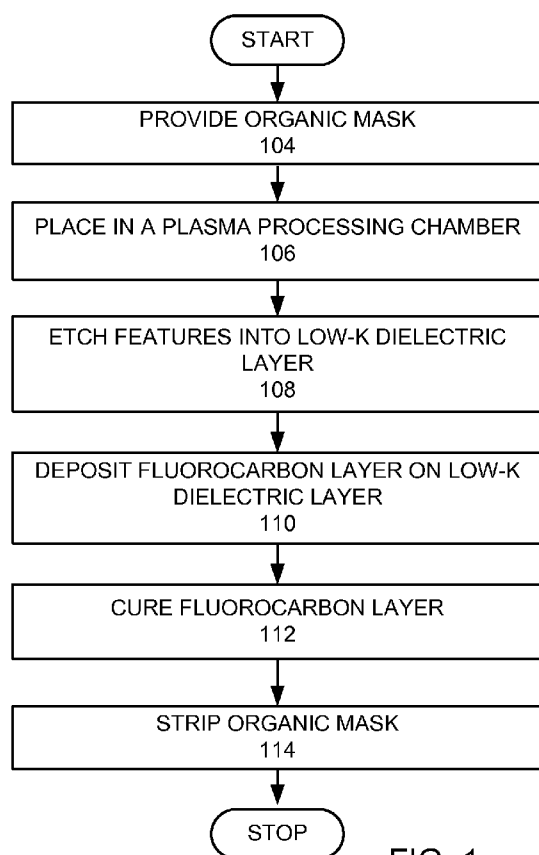


FIG. 1

(57) Abstract: A method for etching features in a low-k dielectric layer disposed below an organic mask is provided by an embodiment of the invention. Features are etched into the low-k dielectric layer through the organic mask. A fluorocarbon layer is deposited on the low-k dielectric layer. The fluorocarbon layer is cured. The organic mask is stripped.



Chewpon Avenue, Milpitas, California 95035 (US).
YEN, Bi-Ming [—/US]; 40495 Carmelita Court, Fremont, California 94539 (US).

(74) **Agents:** LEE, Michael, B., K., Lee et al.; Beyer Law Group LLP, P.O. Box 1687, Cupertino, California 95015-1687 (US).

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